

## **FC119**

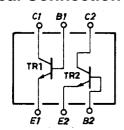
NPN Epitaxial Planar Silicon Transistor

## High-Frequency General-Purpose Amp, **Differential Amp Applications**

#### **Features**

- · Composite type with 2 transistors contained in the CP package currently in use, improving the mounting efficiency greatly.
- · The FC119 is formed with two chips, being equivalent to the 2SC2814, placed in one package.
- · Excellent in thermal equilibrium and pair capability.

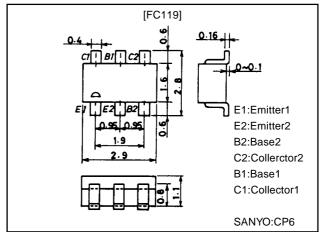
### **Electrical Connection**



## **Package Dimensions**

unit:mm

2068



## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		30	V
Collector-to-Emitter Voltage	VCEO		20	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		5	V
Collector Current	IC		30	mA
Collector Dissipation	PC	1 unit	200	mW
Total Dissipation	PT		300	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to+150	°C

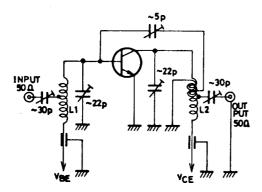
#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Oill
Collector Cutoff Current	ICBO	V <sub>CB</sub> =10V, I <sub>E</sub> =0			0.1	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	80		200	
DC Current Gain Ratio	h <sub>FE</sub> (small/- large)	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	0.8	0.98		
Base to Emitter Voltage Drop	V <sub>BE</sub> (large -small)	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA		1.0	15	mV
Gain-Bandwidth Product	fT	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	200	320		MHz
Reverse Transfer Capacitance	Cre	V <sub>CE</sub> =6V, f=1MHz		0.95	1.2	pF
Base to Collector Time Constant	r <sub>bb</sub> 'c <sub>c</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA, f=31.9MHz			20	ps
Noise Figure	NF	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA, f=100MHz		3.0		dB
Power Gain	PG	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA, f=100MHz		25		dB

Note: The specifications shown above are for each individual transistor.

Marking:119

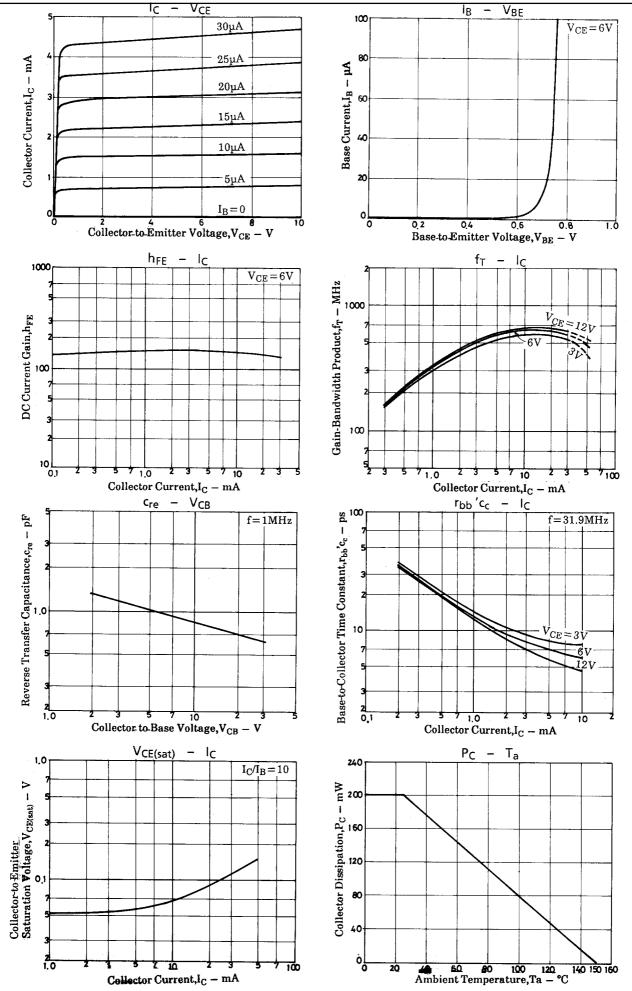
# NF, PG Test Circuit



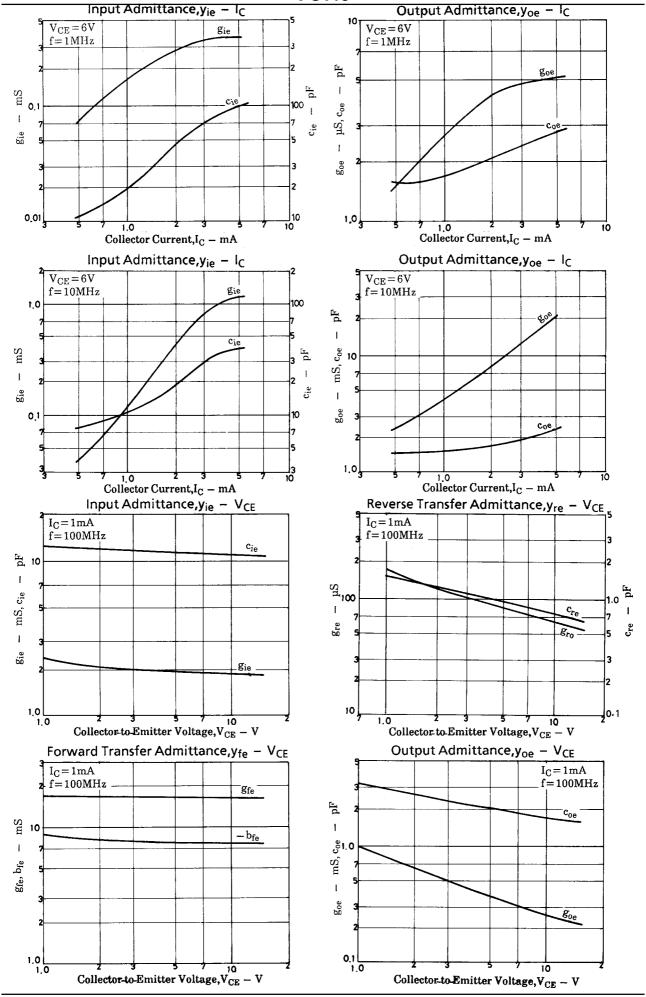
 $\begin{array}{l} L_1: 1mm^{\emptyset} \text{ plated wire, } 10mm^{\emptyset} \text{ 4T, tap: } 2T \text{ from } V_{BE} \text{ side} \\ L_2: 1mm^{\emptyset} \text{ plated wire, } 10mm^{\emptyset} \text{ 7T, tap: } 2T \text{ from } V_{CE} \text{ side} \\ L_3: 1mm^{\emptyset} \text{ enamel wire, } 10mm^{\emptyset} \text{ 3T} \end{array}$ 

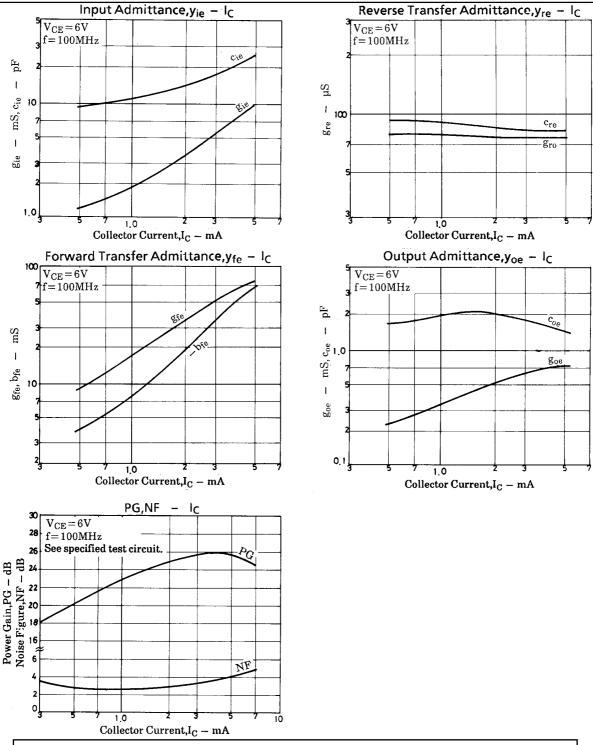
Unit (Capacitance:F)











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